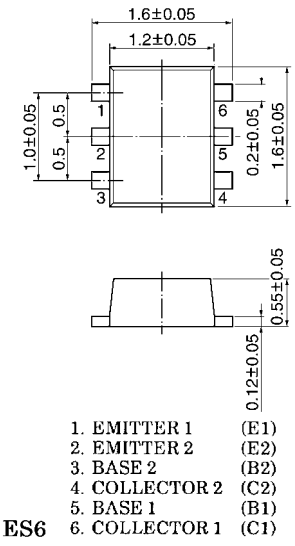
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

RN1961FE,RN1962FE,RN1963FE RN1964FE,RN1965FE,RN1966FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN2961FE~RN2966FE

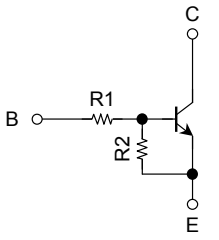
Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-2N1A

Weight: 0.003 g (typ.)

Equivalent Circuit and Bias Resistor Values



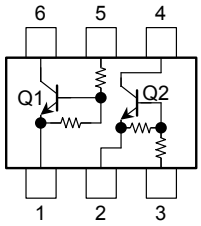
Type No.	R1 (kΩ)	R2 (kΩ)
RN1961FE	4.7	4.7
RN1962FE	10	10
RN1963FE	22	22
RN1964FE	47	47
RN1965FE	2.2	47
RN1966FE	4.7	47

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit
Collector-base voltage	RN1961FE~1966FE	V_{CBO}	50	V
Collector-emitter voltage		V_{CEO}	50	V
Emitter-base voltage	RN1961FE~1964FE	V_{EBO}	10	V
	RN1965FE, 1966FE		5	
Collector current	RN1961FE~RN1966FE	I_C	100	mA
Collector power dissipation		P_C (Note)	100	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: Total rating

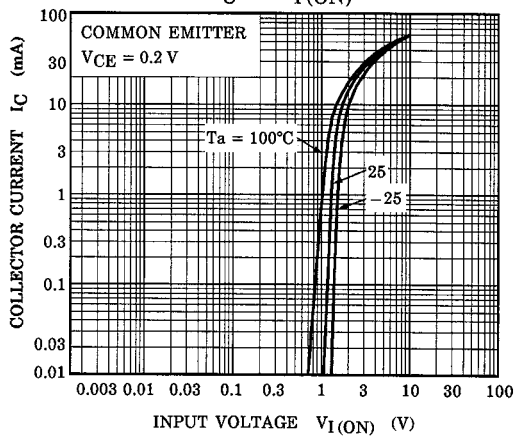
Equivalent Circuit (top view)



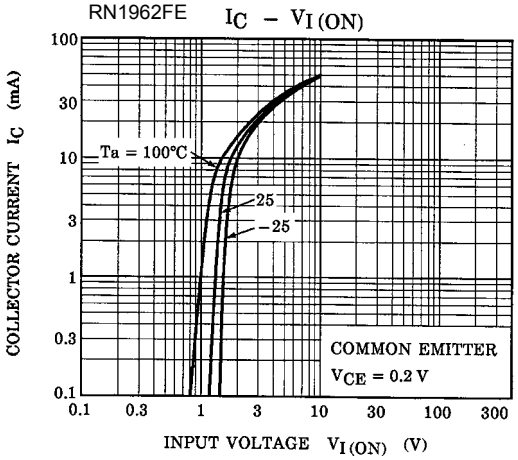
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN1961FE~1966FE	I_{CBO}	V_{CB} = 50 V, I_E = 0	—	—	100	nA
		I_{CEO}	V_{CE} = 50 V, I_B = 0	—	—	500	
Emitter cut-off current	RN1961FE	I_{EBO}	V_{EB} = 10 V, I_C = 0	0.82	—	1.52	mA
	RN1962FE			0.38	—	0.71	
	RN1963FE			0.17	—	0.33	
	RN1964FE			0.082	—	0.15	
	RN1965FE		V_{EB} = 5 V, I_C = 0	0.078	—	0.145	
	RN1966FE			0.074	—	0.138	
DC current gain	RN1961FE	h_{FE}	V_{CE} = 5 V, I_C = 10 mA	30	—	—	
	RN1962FE			50	—	—	
	RN1963FE			70	—	—	
	RN1964FE			80	—	—	
	RN1965FE			80	—	—	
	RN1966FE			80	—	—	
Collector-emitter saturation voltage	RN1961FE~1966FE	$V_{CE\ (sat)}$	I_C = 5 mA, I_B = 0.25 mA	—	0.1	0.3	V
Input voltage (ON)	RN1961FE	$V_{I\ (ON)}$	V_{CE} = 0.2 V, I_C = 5 mA	1.1	—	2.0	V
	RN1962FE			1.2	—	2.4	
	RN1963FE			1.3	—	3.0	
	RN1964FE			1.5	—	5.0	
	RN1965FE			0.6	—	1.1	
	RN1966FE			0.7	—	1.3	
Input voltage (OFF)	RN1961FE~1964FE	$V_{I\ (OFF)}$	V_{CE} = 5 V, I_C = 0.1 mA	1.0	—	1.5	V
	RN1965FE, 1966FE			0.5	—	0.8	
Transition frequency	RN1961FE~1966FE	f_T	V_{CE} = 10 V, I_C = 5 mA	—	250	—	MHz
Collector output capacitance	RN1961FE~1966FE	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	3	6	pF
Input resistor	RN1961FE	R1	—	3.29	4.7	6.11	kΩ
	RN1962FE			7	10	13	
	RN1963FE			15.4	22	28.6	
	RN1964FE			32.9	47	61.1	
	RN1965FE			1.54	2.2	2.86	
	RN1966FE			3.29	4.7	6.11	
Resistor ratio	RN1961FE~1964FE	R1/R2	—	0.9	1.0	1.1	
	RN1965FE			0.0421	0.0468	0.0515	
	RN1966FE			0.09	0.1	0.11	

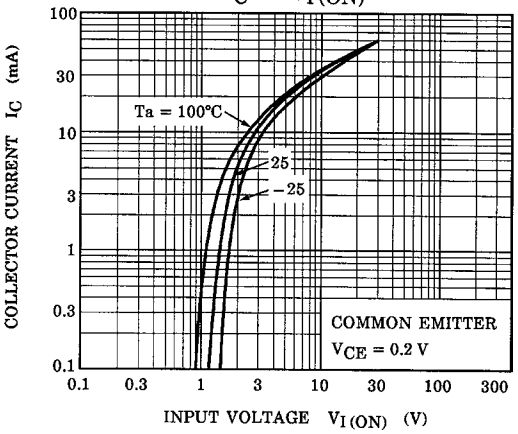
RN1961FE $I_C - V_{I(ON)}$



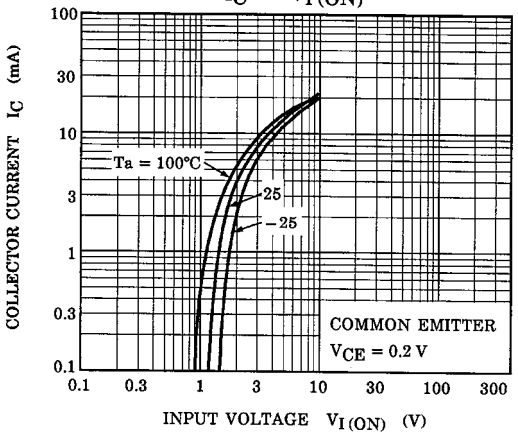
RN1962FE $I_C - V_{I(ON)}$



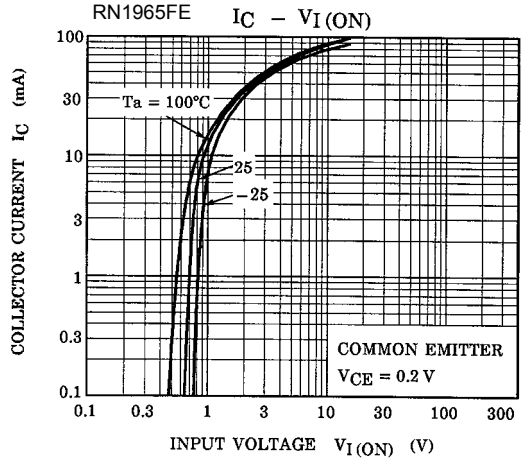
RN1963FE $I_C - V_{I(ON)}$



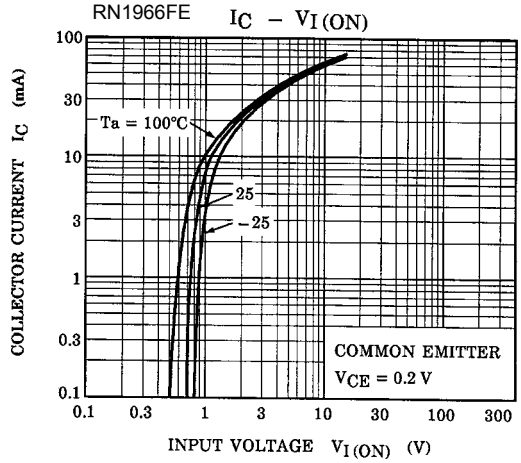
RN1964FE $I_C - V_{I(ON)}$



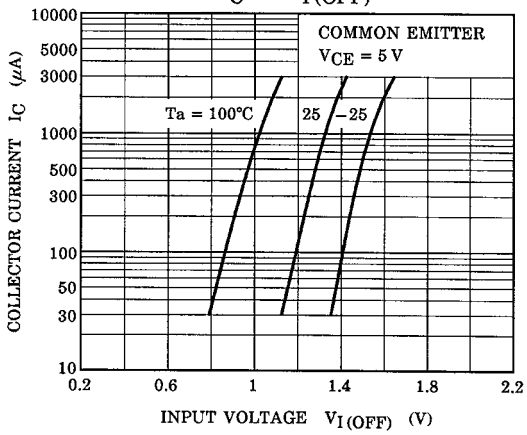
RN1965FE $I_C - V_{I(ON)}$



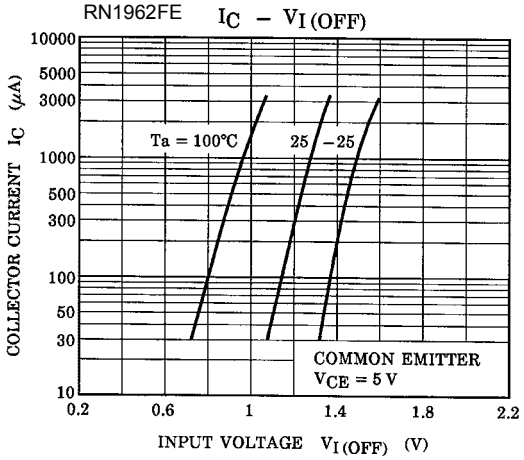
RN1966FE $I_C - V_{I(ON)}$



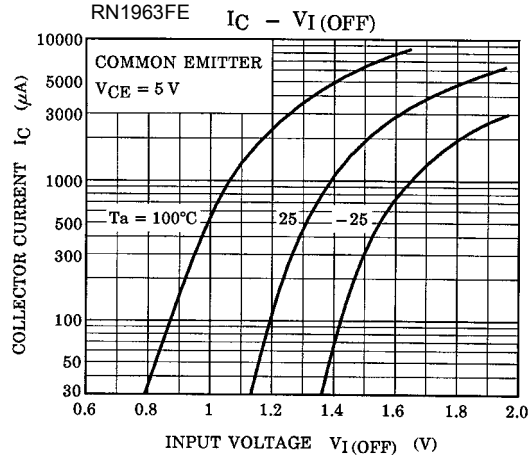
RN1961FE I_C – $V_{I(OFF)}$



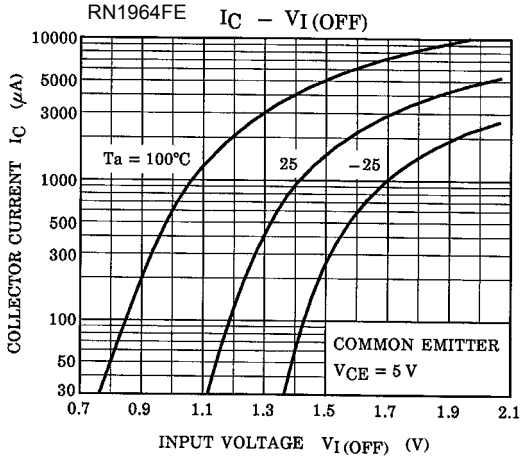
RN1962FE I_C – $V_{I(OFF)}$



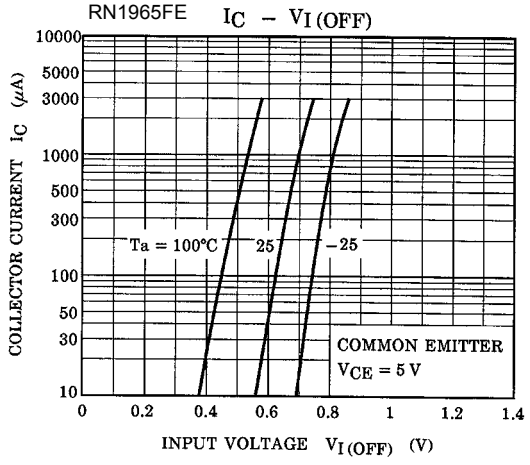
RN1963FE I_C – $V_{I(OFF)}$



RN1964FE I_C – $V_{I(OFF)}$



RN1965FE I_C – $V_{I(OFF)}$



RN1966FE I_C – $V_{I(OFF)}$